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<u>Vishay Semiconductor/Diodes Division</u> <u>VS-8EWF10STRLPBF</u>

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Datasheet of VS-8EWF10STRLPBF - DIODE GEN PURP 1KV 8A DPAK

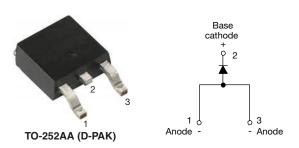
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VS-8EWF..SPbF Soft Recovery Series

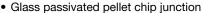
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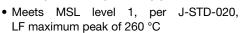
Surface Mount Fast Soft Recovery Rectifier Diode, 8 A



PRODUCT SUMMARY							
TO-252AA (D-PAK)							
8 A							
1000 V, 1200 V							
1.3 V							
150 A							
80 ns							
150 °C							
Single die							
0.6							

FEATURES







 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS

APPLICATIONS

- Output rectification and freewheeling diode in inverters, choppers and converters
- Input rectifications where severe restrictions on conducted EMI should be met

DESCRIPTION

The VS-8EWF..S-M3 fast soft recovery rectifier series has been optimized for combined short reverse recovery time, low forward voltage drop and low leakage current.

The glass passivation ensures stable reliable operation in the most severe temperature and power cycling conditions.

MAJOR RATINGS AND CHARACTERISTICS									
SYMBOL	CHARACTERISTICS	VALUES	UNITS						
I _{F(AV)}	Sinusoidal waveform	8	А						
V _{RRM}		1000/1200	V						
I _{FSM}		150	А						
V _F	8 A, T _J = 25 °C	1.3	V						
t _{rr}	1 A, 100 A/μs	80	ns						
TJ	Range	-40 to +150	°C						

VOLTAGE RATINGS			
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} AT 150 °C mA
VS-8EWF10SPbF	1000	1100	4
VS-8EWF12SPbF	1200	1300	4

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Maximum average forward current	I _{F(AV)}	T _C = 94 °C, 180° conduction half sine wave	8						
Maximum peak one cycle	I _{FSM}	10 ms sine pulse, rated V _{RRM} applied	125	Α					
non-repetitive surge current		10 ms sine pulse, no voltage reapplied	150	l					
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rated V _{RRM} applied	78	A ² s					
waximum i-t for fusing		10 ms sine pulse, no voltage reapplied	110	A-5					
Maximum l²√t for fusing	I ² √t	t = 0.1 to 10 ms, no voltage reapplied	1100	A²√s					

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ELECTRICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST COI	VALUES	UNITS					
Maximum forward voltage drop	V_{FM}	8 A, T _J = 25 °C	1.3	V					
Forward slope resistance	r _t	T. ₁ = 150 °C	25.6	mΩ					
Threshold voltage	V _{F(TO)}	1J = 150 C	0.93	V					
Maximum reverse leakage current	l	$T_J = 25 ^{\circ}\text{C}$		0.1	mA				
Maximum reverse leakage current	IRM	T _J = 150 °C	V _R = Rated V _{RRM}	4	IIIA				

RECOVERY CHARACTERISTICS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	· •					
Reverse recovery time	t _{rr}	I _F at 8 A _{pk}	270	ns	I _{FM} t					
Reverse recovery current	I _{rr}	25 A/µs	4.2	Α	$t_a \mid t_b$					
Reverse recovery charge	Q _{rr}	T _J = 25 °C	1	μC	di / Q _{rr}					
Snap factor	S		0.6		V V V V V V V V V V					

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +150	°C				
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	2.5	°C/W				
Typical thermal resistance, junction to ambient (PCB mount)	R _{thJA} ⁽¹⁾		50	C/VV				
Soldering temperature	T _S	For 10 s	260	°C				
Approximate weight			1	g				
Approximate weight			0.03	OZ.				
Marking device		Case style TO-252AA (D-PAK)	8EWF	-12S				

Note

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 $^{^{(1)}}$ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μ m) copper 40 °C/W For recommended footprint and soldering techniques refer to application note #AN-994

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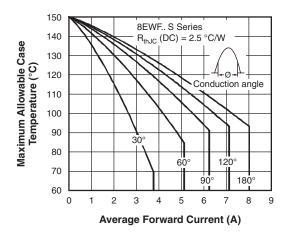


Fig. 1 - Current Rating Characteristics

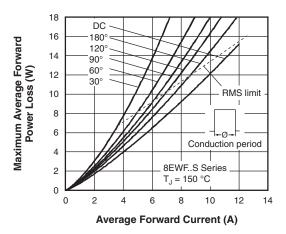


Fig. 4 - Forward Power Loss Characteristics

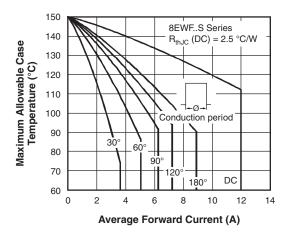


Fig. 2 - Current Rating Characteristics

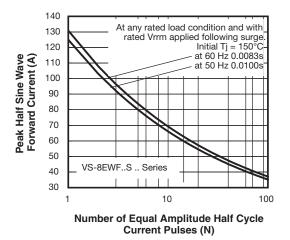


Fig. 5 - Maximum Non-Repetitive Surge Current

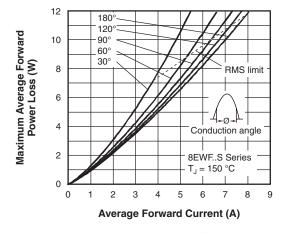


Fig. 3 - Forward Power Loss Characteristics

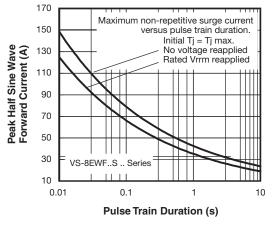


Fig. 6 - Maximum Non-Repetitive Surge Current

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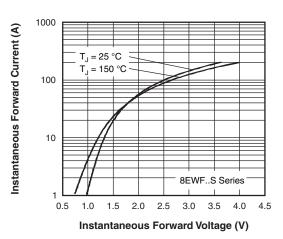


Fig. 7 - Forward Voltage Drop Characteristics

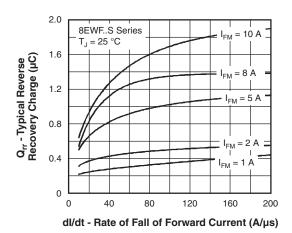


Fig. 10 - Recovery Charge Characteristics, T_J = 25 °C

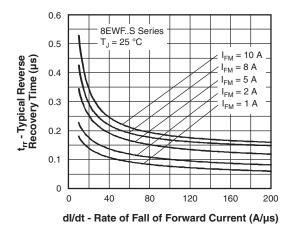


Fig. 8 - Recovery Time Characteristics, T_J = 25 °C

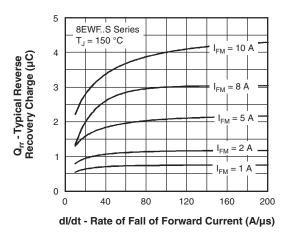


Fig. 11 - Recovery Charge Characteristics, T_J = 150 °C

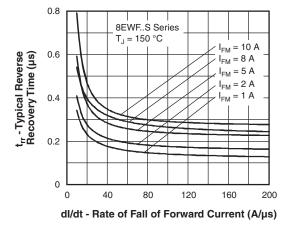


Fig. 9 - Recovery Time Characteristics, T_J = 150 °C

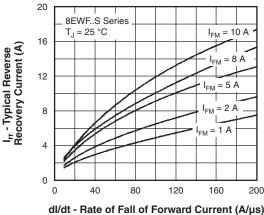


Fig. 12 - Recovery Current Characteristics, T_J = 25 °C

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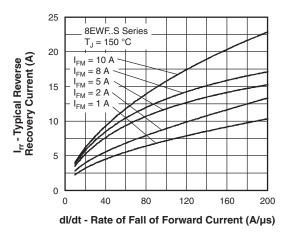


Fig. 13 - Recovery Current Characteristics, T_J = 150 °C

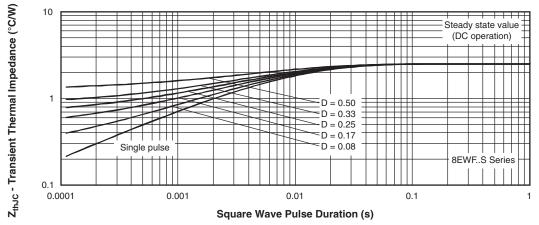


Fig. 14 - Thermal Impedance Z_{thJC} Characteristics

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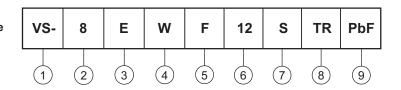


VS-8EWF..SPbF Soft Recovery Series

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ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

2 - Current rating (8 = 8 A)

3 - Circuit configuration:

E = single diode

4 - Package:

W = D-PAK

5 - Type of silicon:

F = fast soft recovery rectifier

6 - Voltage code x 100 = V_{RRM} - 10 = 1000 V 12 = 1200 V

7 - S = surface mountable

8 - • TR = tape and reel

• TRR = tape and reel (right oriented)

• TRL = tape and reel (left oriented)

9 - None = standard production

• PbF = lead (Pb)-free

LINKS TO RELATED DOCUMENTS							
Dimensions <u>www.vishay.com/doc?95016</u>							
Part marking information	www.vishay.com/doc?95059						
Packaging information	www.vishay.com/doc?95033						
SPICE model	www.vishay.com/doc?95552						

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For technical questions within your region: Diodes Americas @vishay.com Diodes Asia@vishay.com Diodes Europe@vishay.com Diodes Europe@vishay.com Diodes Europe@vishay.com

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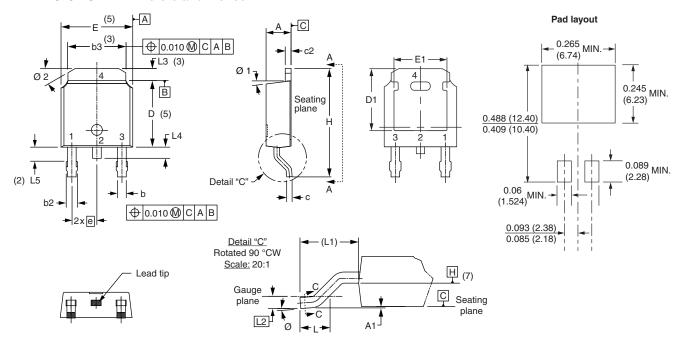


Outline Dimensions

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D-PAK (TO-252AA)

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	2.18	2.39	0.086	0.094			е	2.29	BSC	0.090	BSC	
A1	-	0.13	-	0.005			Н	9.40	10.41	0.370	0.410	
b	0.64	0.89	0.025	0.035			L	1.40	1.78	0.055	0.070	
b2	0.76	1.14	0.030	0.045			L1	2.74	BSC	0.108	REF.	
b3	4.95	5.46	0.195	0.215	3		L2	0.51	BSC	0.020) BSC	
С	0.46	0.61	0.018	0.024			L3	0.89	1.27	0.035	0.050	3
c2	0.46	0.89	0.018	0.035			L4		1.02		0.040	
D	5.97	6.22	0.235	0.245	5		L5	1.14	1.52	0.045	0.060	2
D1	5.21	-	0.205	-	3		Ø	0°	10°	0°	10°	
Е	6.35	6.73	0.250	0.265	5		Ø1	0°	15°	0°	15°	
E1	4.32	-	0.170	-	3		Ø2	25°	35°	25°	35°	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension uncontrolled in L5
- (3) Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- (4) Section C C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- (5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (6) Dimension b1 and c1 applied to base metal only
- $^{(7)}$ Datum A and B to be determined at datum plane H
- (8) Outline conforms to JEDEC outline TO-252AA



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